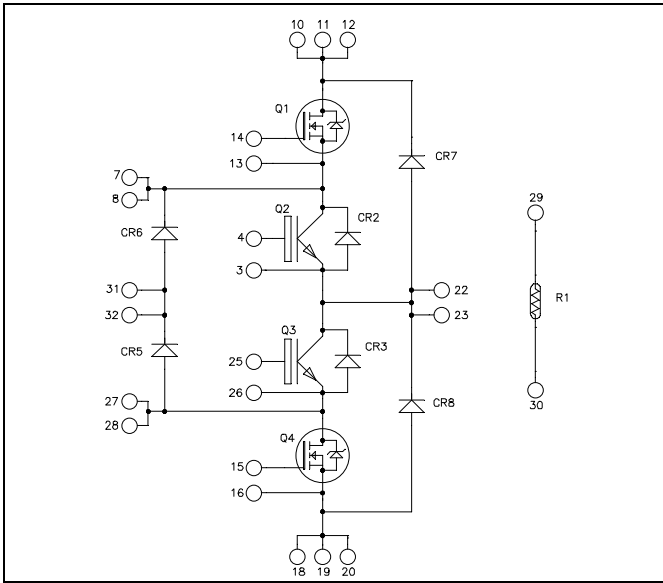


*Three level inverter
CoolMOS & Trench + Field Stop IGBT
Power Module*

Trench & Field Stop IGBT Q2, Q3:
 $V_{CES} = 600V$; $I_C = 30A$ @ $T_c = 80^\circ C$

CoolMOS™ Q1, Q4:
 $V_{DSS} = 600V$; $I_D = 17A$ @ $T_c = 80^\circ C$



Application

- Solar converter
- Uninterruptible Power Supplies

Features

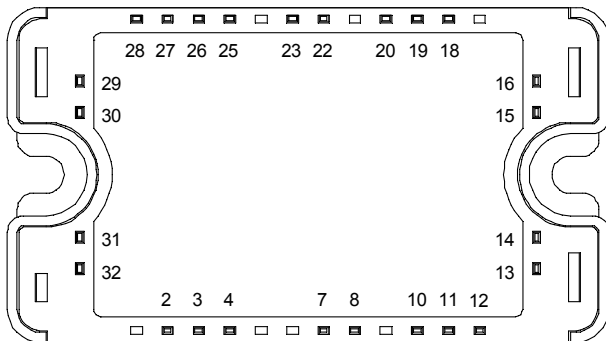
- **Q2, Q3 Trench + Field Stop IGBT Technology**
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated

- **Q1, Q4 CoolMOS™**
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged

- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of V_{CEsat}
- Low profile
- RoHS Compliant



All multiple inputs and outputs must be shorted together
 Example: 10/11/12 ; 7/8 ...

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.
 See application note APT0502 on www.microsemi.com

Q1 & Q4 Absolute maximum ratings

<i>Symbol</i>	<i>Parameter</i>	<i>Max ratings</i>	<i>Unit</i>
V _{DSS}	Drain - Source Breakdown Voltage	600	V
I _D	Continuous Drain Current	T _c = 25°C	22
		T _c = 80°C	17
I _{DM}	Pulsed Drain current	75	A
V _{GS}	Gate - Source Voltage	±20	V
R _{DS(on)}	Drain - Source ON Resistance	99	mΩ
P _D	Maximum Power Dissipation	T _c = 25°C	110
I _{AR}	Avalanche current (repetitive and non repetitive)	11	A
E _{AR}	Repetitive Avalanche Energy	1.2	mJ
E _{AS}	Single Pulse Avalanche Energy	800	

Q1 & Q4 Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0V V _{DS} = 600V	T _j = 25°C		50	μA
			T _j = 125°C		100	
R _{DS(on)}	Drain – Source on Resistance	V _{GS} = 10V, I _D = 18A			99	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 1.2 mA	2.5	3	3.5	V
I _{GSS}	Gate – Source Leakage Current	V _{GS} = ±20 V, V _{DS} = 0V			100	nA

Q1 & Q4 Dynamic Characteristics
Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C _{iss}	Input Capacitance	V _{GS} = 0V ; V _{DS} = 100V f = 1MHz		2800		pF
C _{oss}	Output Capacitance			130		
Q _g	Total gate Charge	V _{GS} = 10V V _{Bus} = 400V I _D = 18A		14		nC
Q _{gs}	Gate – Source Charge			20		
Q _{gd}	Gate – Drain Charge			60		
T _{d(on)}	Turn-on Delay Time	V _{GS} = 10V V _{Bus} = 400V I _D = 18A R _G = 3.3Ω		10		ns
T _r	Rise Time			5		
T _{d(off)}	Turn-off Delay Time			60		
T _f	Fall Time			5		
R _{thJC}	Junction to Case Thermal Resistance				1.15	°C/W

Q2 & Q3 Absolute maximum ratings

<i>Symbol</i>	<i>Parameter</i>	<i>Max ratings</i>	<i>Unit</i>
V _{CES}	Collector - Emitter Breakdown Voltage	600	V
I _C	Continuous Collector Current	T _c = 25°C	50
		T _c = 80°C	30
I _{CM}	Pulsed Collector Current	T _c = 25°C	60
V _{GE}	Gate – Emitter Voltage	±20	V
P _D	Maximum Power Dissipation	T _c = 25°C	90
RBSOA	Reverse Bias Safe Operating Area	T _J = 150°C	60A @ 550V

Q2 & Q3 Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 30A$	$T_j = 25^\circ C$	1.5	1.9	V
			$T_j = 150^\circ C$	1.7		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 400\mu A$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			300	nA

Q2 & Q3 Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C_{ies}	Input Capacitance	$V_{GE} = 0V$		1600		pF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		110		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		50		
Q_G	Gate charge	$V_{GE} = \pm 15V, I_C = 30A$ $V_{CE} = 300V$		0.3		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 30A$ $R_G = 10\Omega$		110		ns
T_r	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			200		
T_f	Fall Time			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 30A$ $R_G = 10\Omega$		120		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			250		
T_f	Fall Time			60		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$	$T_j = 25^\circ C$	0.16		mJ
			$T_j = 150^\circ C$	0.3		
E_{off}	Turn-off Switching Energy	$I_C = 30A$ $R_G = 10\Omega$	$T_j = 25^\circ C$	0.7		mJ
			$T_j = 150^\circ C$	1.05		
I_{sc}	Short Circuit data	$V_{GE} \leq 15V ; V_{Bus} = 360V$ $t_p \leq 6\mu s ; T_j = 150^\circ C$		150		A
R_{thJC}	Junction to Case Thermal Resistance				1.6	$^\circ C/W$

CR5 & CR6 diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	T _j = 25°C			25	μA
			T _j = 125°C			500	
I _F	DC Forward Current	T _c = 80°C			30		A
V _F	Diode Forward Voltage	I _F = 30A			1.8	2.2	V
		I _F = 60A			2.2		
		I _F = 30A	T _j = 125°C		1.5		
t _{rr}	Reverse Recovery Time	I _F = 30A V _R = 400V di/dt = 200A/μs	T _j = 25°C		25		ns
			T _j = 125°C		160		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		35		nC
			T _j = 125°C		480		
E _{rr}	Reverse Recovery Energy	I _F = 30A V _R = 400V di/dt = 1000A/μs	T _j = 125°C		0.6		mJ
R _{thJC}	Junction to Case Thermal Resistance					1.2	°C/W

CR2, CR3, CR7 & CR8 diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Maximum Reverse Leakage Current	V _R =1200V	T _j = 25°C			100	μA
			T _j = 125°C			500	
I _F	DC Forward Current	T _c = 80°C			30		A
V _F	Diode Forward Voltage	I _F = 30A			2.6	3.1	V
		I _F = 60A			3.2		
		I _F = 30A	T _j = 125°C		1.8		
t _{rr}	Reverse Recovery Time	I _F = 30A V _R = 800V di/dt = 200A/μs	T _j = 25°C		300		ns
			T _j = 125°C		380		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		360		nC
			T _j = 125°C		1700		
E _{rr}	Reverse Recovery Energy	I _F = 30A V _R = 800V di/dt = 1000A/μs	T _j = 125°C		1.6		mJ
R _{thJC}	Junction to Case Thermal Resistance					1.2	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C =100°C		4		%

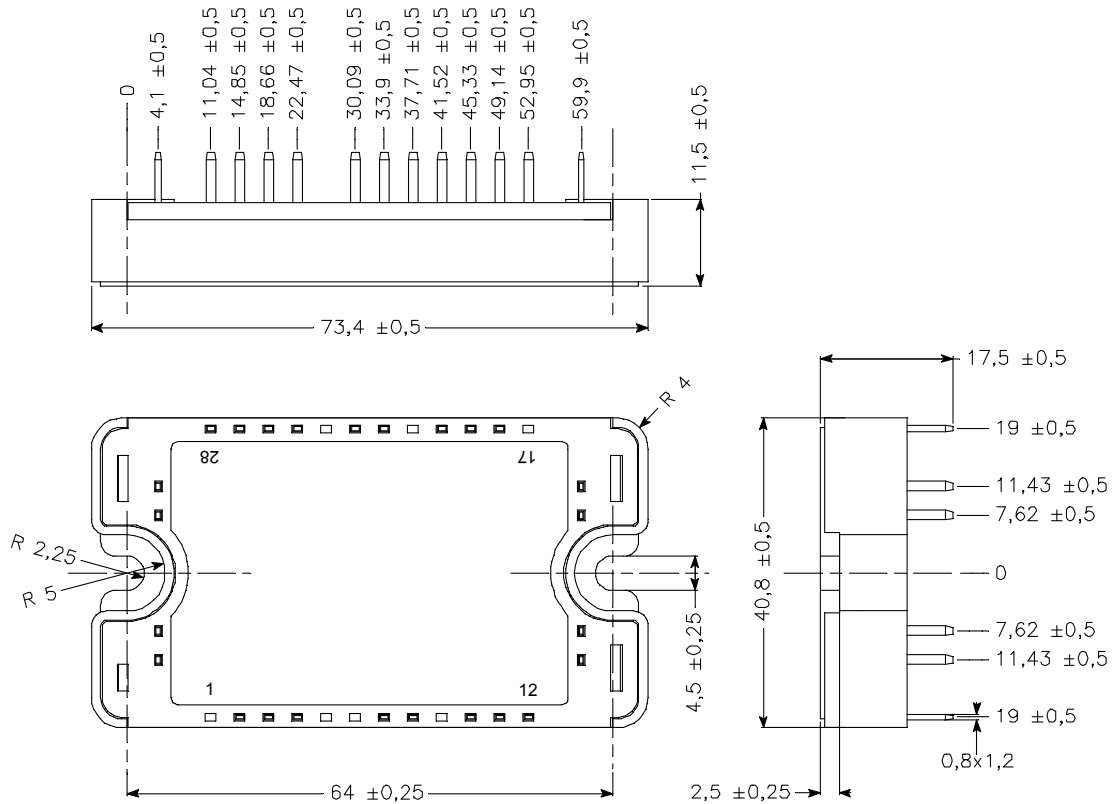
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

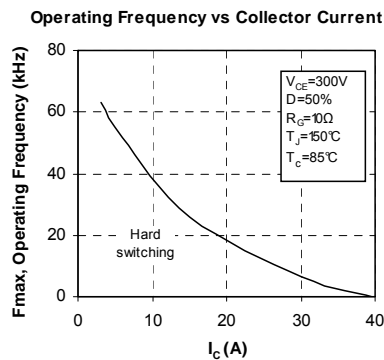
Thermal and package characteristics

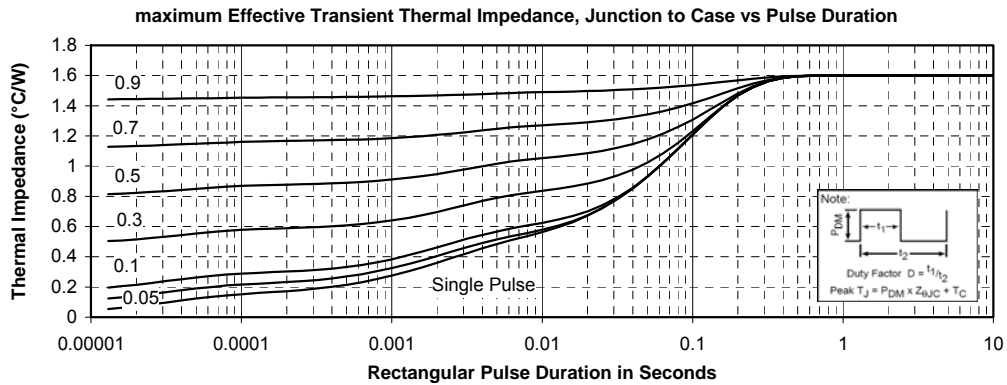
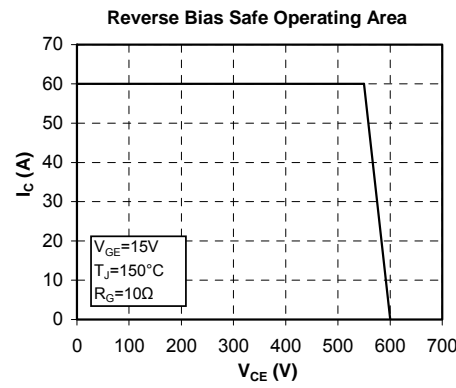
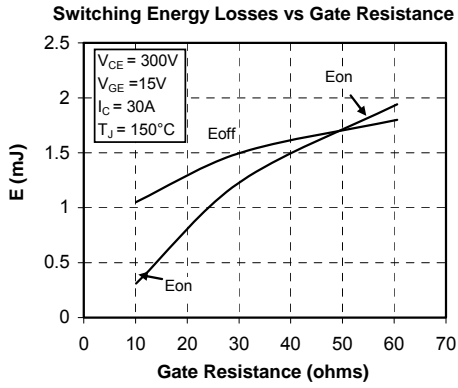
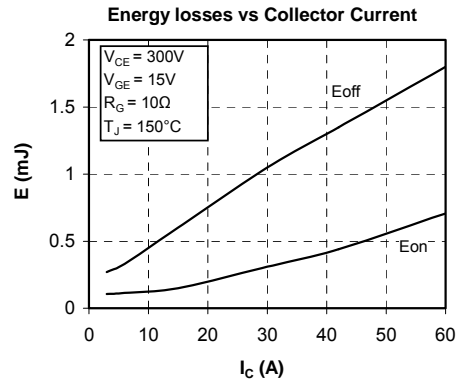
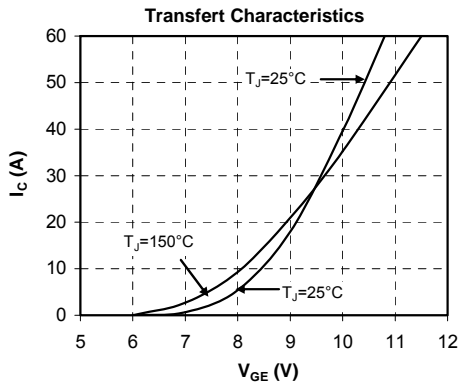
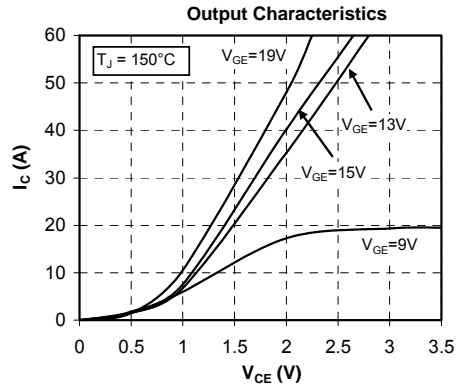
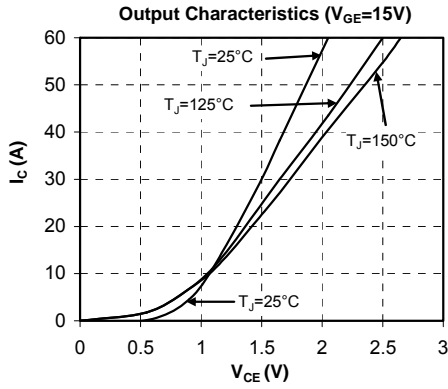
Symbol	Characteristic	Min	Typ	Max	Unit	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		175*	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

* T_{jmax} = 150°C for Q1 & Q4

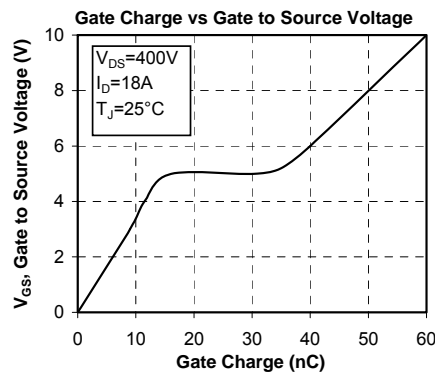
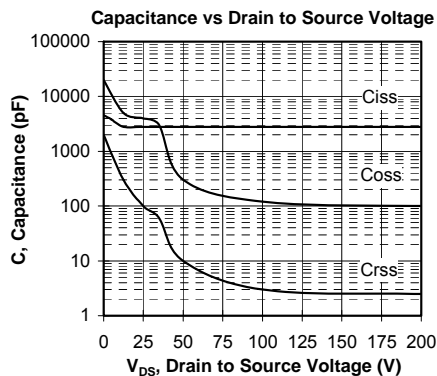
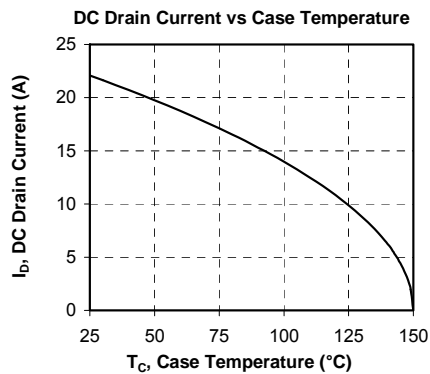
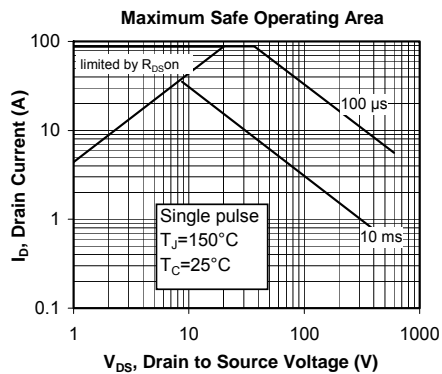
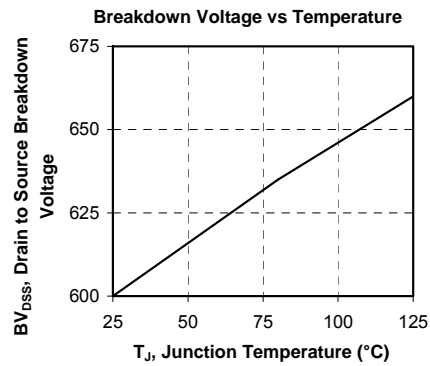
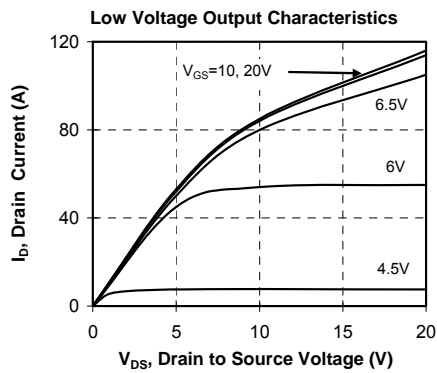
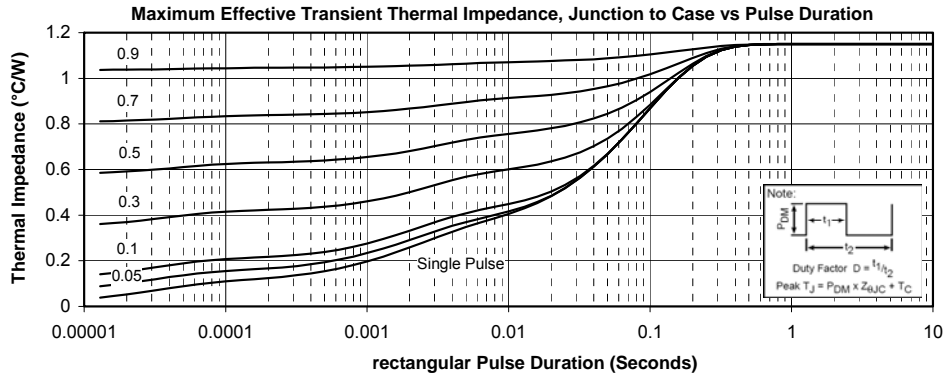
SP3 Package outline (dimensions in mm)


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

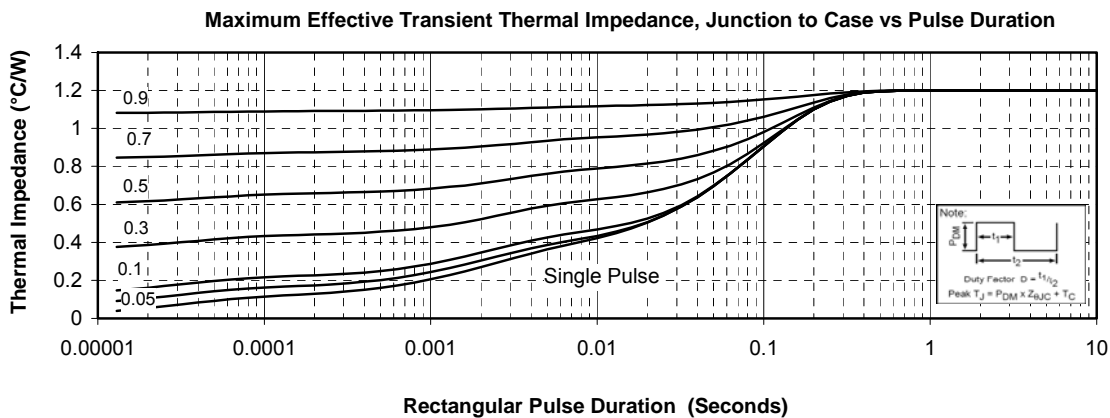
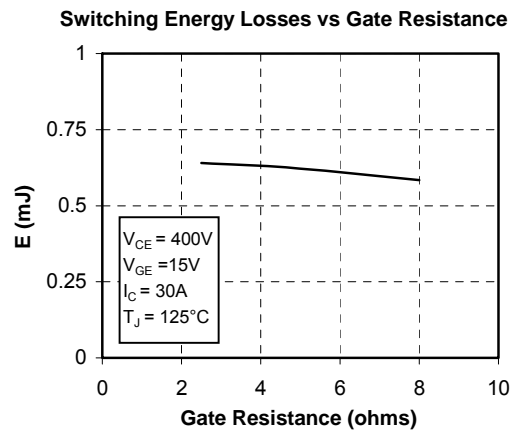
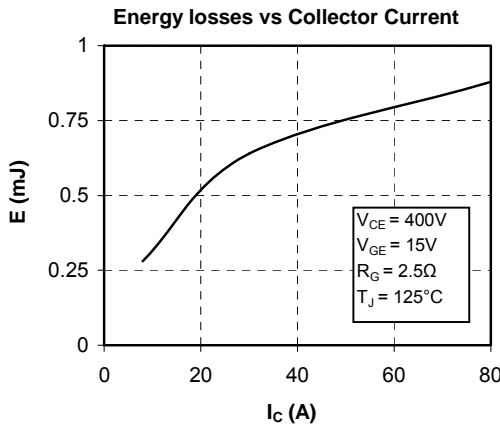
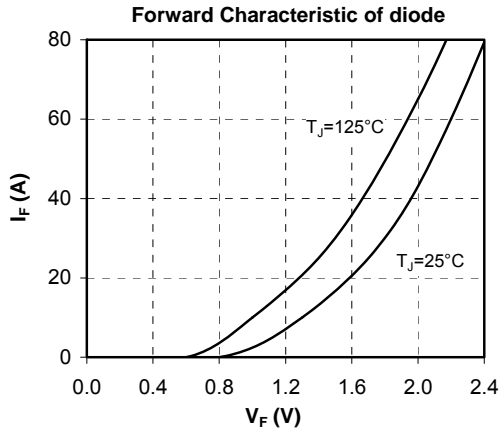
Q2 & Q3 Typical performance curve


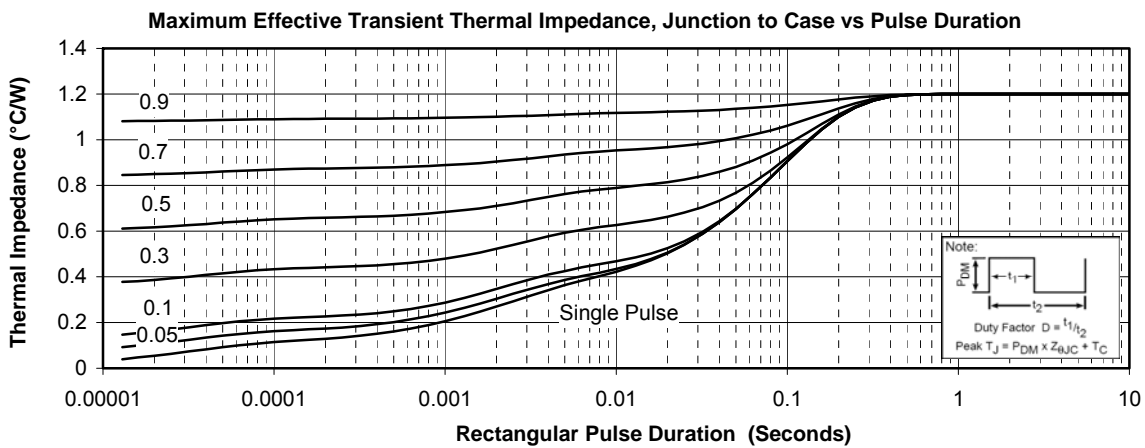
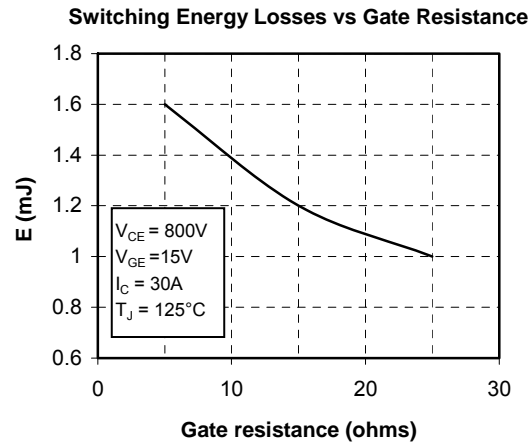
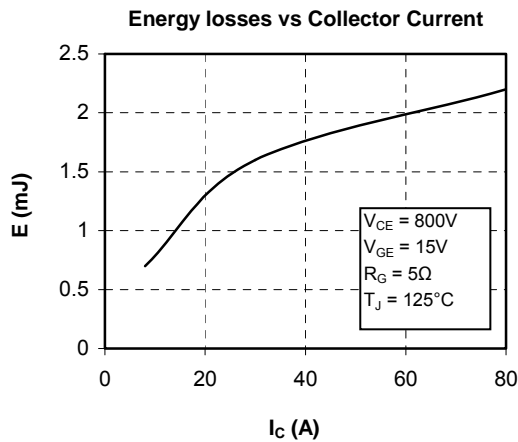
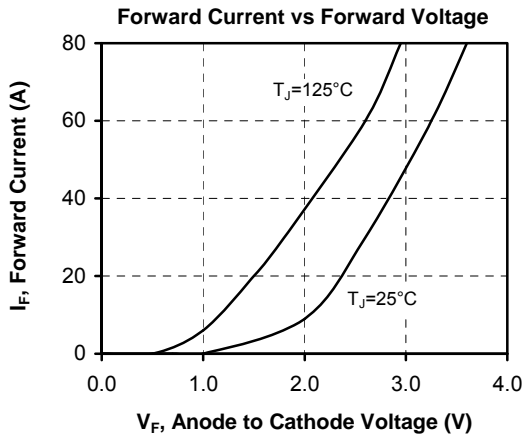


Q1 & Q4 Typical performance curve



CR5 & CR6 Typical performance curve



CR2, CR3, CR7 & CR8 Typical performance curve


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